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SiO<sub>2</sub> Etch using ICP2 with O<sub>2</sub>

Recipe (#104): 0.5Pa, 50/500W, CHF<sub>3</sub>/CF<sub>4</sub>/O<sub>2</sub>=35/5/10 sccm, time=3.5 min (210 sec)

1) Run#01 (10-5-2018)

Etch rate=95.2 nm/min, Etch Selectivity (SiO<sub>2</sub>/PR) =0.74, Averaged Sidewall Angle=77.9°.

Figure 1 (a), (b), and (c) SiO<sub>2</sub> etch profile; (d) PR etch-mask profile.



